FAIRCHILD SEMICONDUCTOR

FPDB20PH60

Smart Power Module for Front-End Rectifier

General Description

FPDB20PH60 is an advanced smart power module of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is futher enhanced by the integrated under-voltage lock-out and over-current protection function.

Features

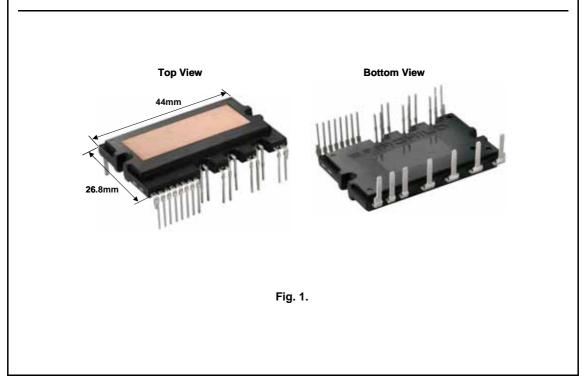
- Low thermal resistance due to Al₂O₃-DBC substrate
- 600V-20A 2-phase IGBT PWM semi-converter including a drive IC for gate driving and protection

January, 2006

- Typical switching frequency of 20kHz
- Isolation rating of 2500Vrms/min.

Applications

• AC 180V ~ 264V single-phase front-end rectifier



©2005 Fairchild Semiconductor Corporation

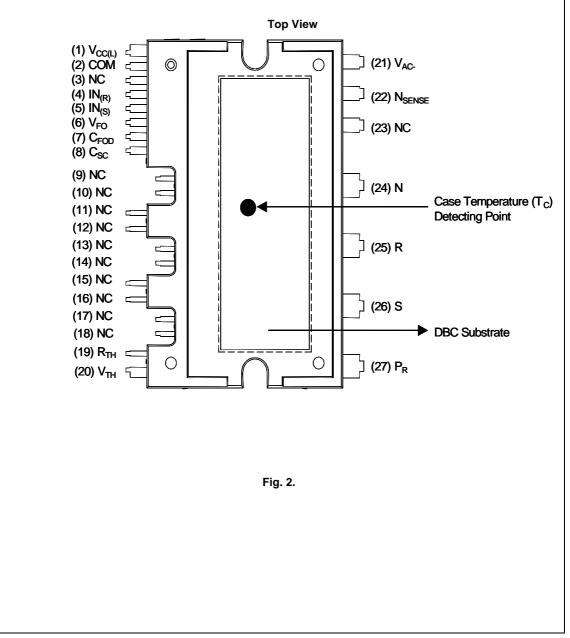
Integrated Power Functions

• PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

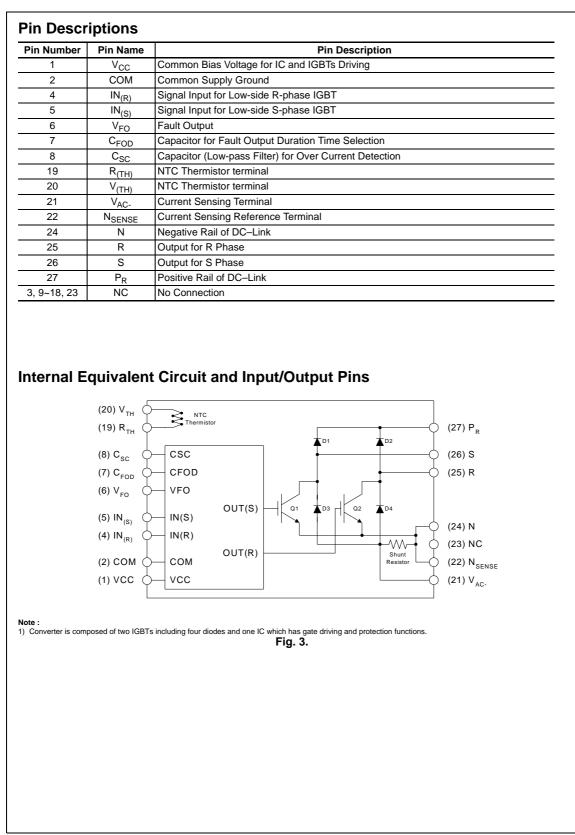
Integrated Drive, Protection and System Control Functions

- For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

Pin Configuration



©2005 Fairchild Semiconductor Corporation



FPDB20PH60

©2005 Fairchild Semiconductor Corporation

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified) **Converter Part**

ltem	Symbol	Condition	Rating	Unit	
Supply Voltage	Vi	Applied between R-S	264	V _{RMS}	
Supply Voltage (Surge)	V _{i(Surge)}	Applied between R-S	500	V	
Output Voltage	V _{PN}	Applied between P- N	450	V	
Output Voltage (Surge)	V _{PN(Surge)}	Applied between P- N	500	V	
Collector-emitter Voltage	V _{CES}		600	V	
Input Current (100% Load)	li	T _C < 95°C, V _i =220V, V _{PN} = 390V, V _{PWM} =20kHz	12	A	
Input Current (125% Load)	I _{i(125%)}	T _C < 95°C, V _i =220V, V _{PN} = 390V, V _{PWM} =20kHz, 1min Non-repetitive	15	A	
Collector Dissipation	P _C	T _C = 25°C per One IGBT	62.5	W	
Power Rating of Shunt Resistor	P _{RSH}	T _C < 125°C	1.5	W	
Operating Junction Temperature	ТJ	T _{.1} (Note 1)		°C	

Note 1. The maximum junction temperature rating of the power chips integrated within the SPM is 150 °C(@T_C \leq 100°C). However, to insure safe operation of the SPM, the average junction temperature should be limited to T_{J(ave)} \leq 125°C (@T_C \leq 100°C).

Control Part

ltem	Symbol	Condition	Rating	Unit
Control Supply Voltage	V _{CC}	Applied between V _{CC} - COM	20	V
Input Signal Voltage	V _{IN}	Applied between IN - COM	-0.3~5.5	V
Fault Output Supply Voltage	V _{FO}	Applied between V _{FO} - COM	-0.3~V _{CC} +0.3	V
Fault Output Current	I _{FO}	Sink Current at V _{FO} Pin	5	mA
Current Sensing Input Voltage	V _{SC}	Applied between C _{SC} - COM	-0.3~V _{CC} +0.3	V

Total System

Item	Symbol	Condition	Rating	Unit
Module Case Operation Temperature	Т _С		-20 ~ 100	°C
Storage Temperature	T _{STG}		-40 ~ 125	°C
Isolation Voltage	V _{ISO}	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V _{rms}

Thermal Resistance

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to Case Thermal	R _{θ(j-c)Q}	IGBT	-	-	1.6	°C/W
Resistance	R _{θ(j-c)HD}	High-side diode	-	-	2.4	°C/W
(Referenced to chip center)	$R_{\theta(j-c)LD}$	Low-side diode	-	-	1.9	°C/W

Note :

2. For the measurement point of case temperature(T_C), please refer to Fig. 2.

©2005 Fairchild Semiconductor Corporation

Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified) **Converter Part**

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
IGBT saturation voltage	V _{CE(sat)}	V _{CC} =15V, V _{IN} = 5V; I _C =20A	-	2.4	3.0	V
High-side diode voltage	V _{FH}	I _F = 20A	-	1.9	2.7	V
Low-side diode voltage	V _{FL}	I _F = 20A	-	1.1	1.5	V
Switching Times	t _{ON}	V _{PN} = 400V, V _{CC} = 15V, I _C =20A	-	690	-	ns
-	t _{C(ON)}	$V_{IN} = 0V \leftrightarrow 5V$, Inductive Load	-	510	-	ns
	t _{OFF}	(Note 3)	-	450	-	ns
-	t _{C(OFF)}		-	120	-	ns
-	t _{rr}		-	50	-	ns
	I _{rr}		-	2	-	Α
Current sensing resistor	R _{SENSE}		3.6	4.0	4.4	mΩ
Collector - emitter Leakage Current	I _{CES}	$V_{CE} = V_{CES}$	-	-	250	μΑ

Note
t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. t_{C(ON)} and t_{C(OFF)} are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

Control Part

Item	Symbol	C	ondition	Min.	Тур.	Max.	Unit
Quiescent V _{CC} Supply Current	IQCCL	V _{CC} = 15V, IN = 0V	V _{CC} - COM	-	-	26	mA
Fault Output Voltage	V _{FOH}	V _{SC} = 0V, V _{FO} Circui	t: 4.7kΩ to 5V Pull-up	4.5	-	-	V
	V _{FOL}	V _{SC} = 1V, V _{FO} Circui	t: 4.7kΩ to 5V Pull-up	-	-	0.8	V
Over Current Trip Level	V _{SC(ref)}	V _{CC} = 15V		0.45	0.5	0.55	V
Supply Circuit Under-	UV _{CCD}	Detection Level		10.7	11.9	13.0	V
Voltage Protection	UV _{CCR}	Reset Level		11.2	12.4	13.2	V
Fault-out Pulse Width	t _{FOD}	C _{FOD} = 33nF (Note 4)		1.4	1.8	2.0	ms
ON Threshold Voltage	V _{IN(ON)}	Applied between IN - COM		3.0	-	-	V
OFF Threshold Voltage	V _{IN(OFF)}			-	-	0.8	V
Resistance of Thermistor	R _{TH}	@ T _C = 25°C (Note Fig. 9)		-	50	-	kΩ
		@ T _C = 80°C (Note F	Fig. 9)	-	5.76	-	kΩ

Note 4. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

FPDB20PH60

©2005 Fairchild Semiconductor Corporation



Mechanical Characteristics and Ratings

ltem		Condition		Limits		
nem		Condition		Тур.	Max.	Units
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N•m	0.51	0.62	0.72	N∙m
Device Flatness	Note Fig. 5		0	-	+120	μm
Weight			-	15.00	-	g

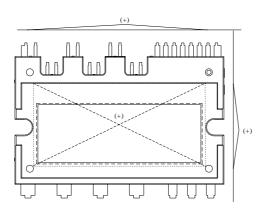
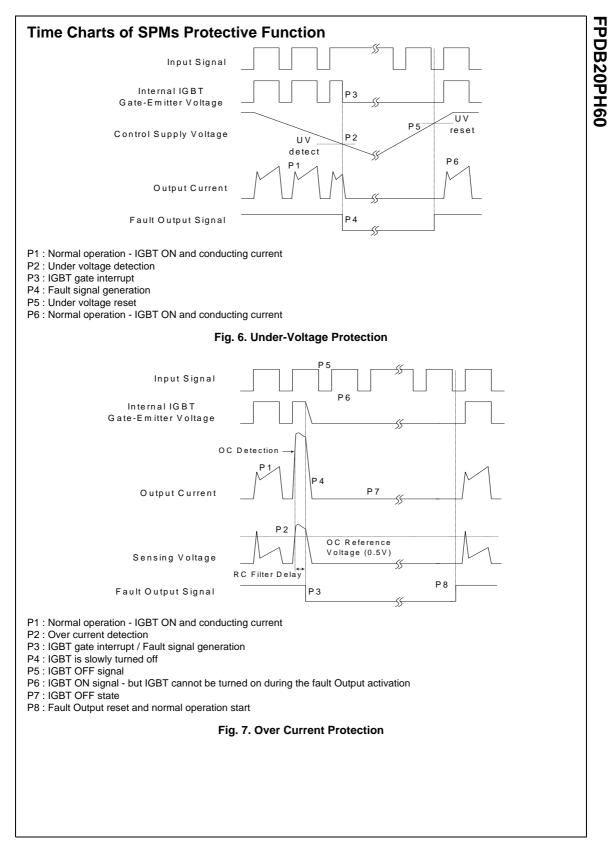
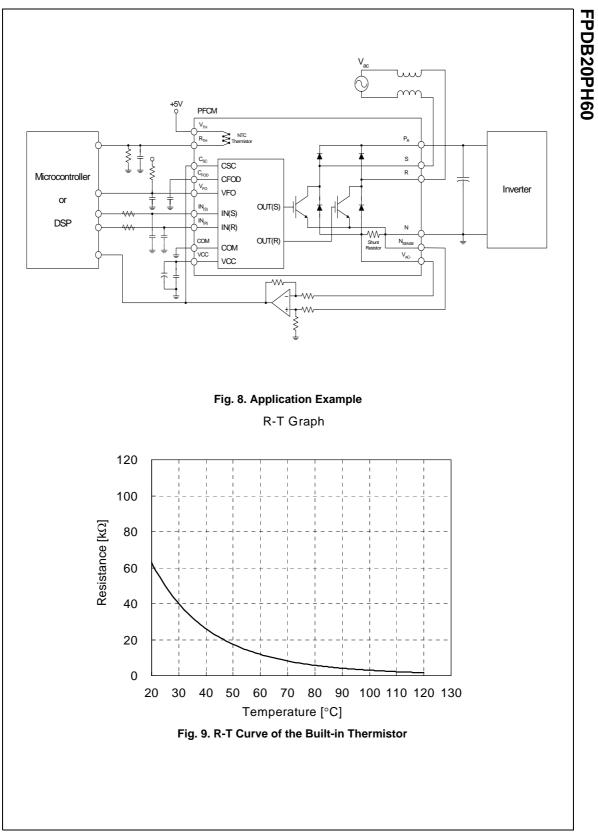


Fig. 5. Flatness Measurement Position

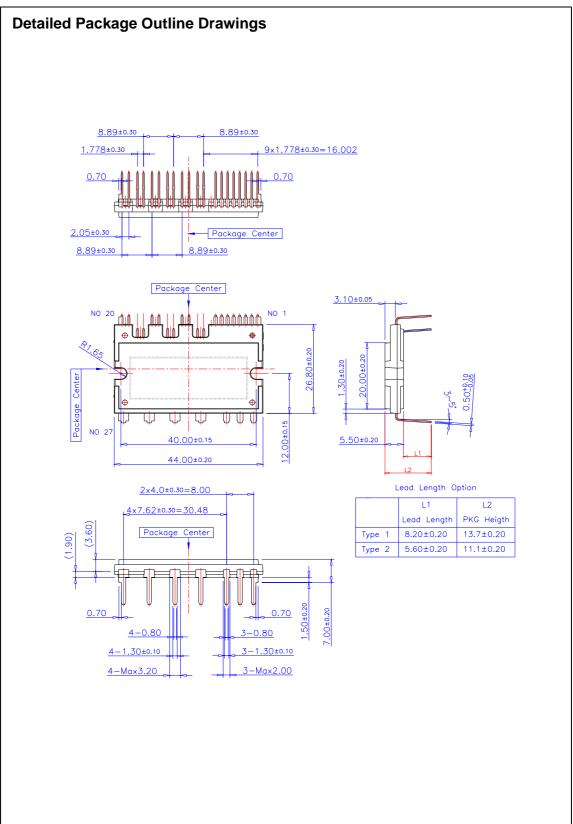
FPDB20PH60



©2005 Fairchild Semiconductor Corporation

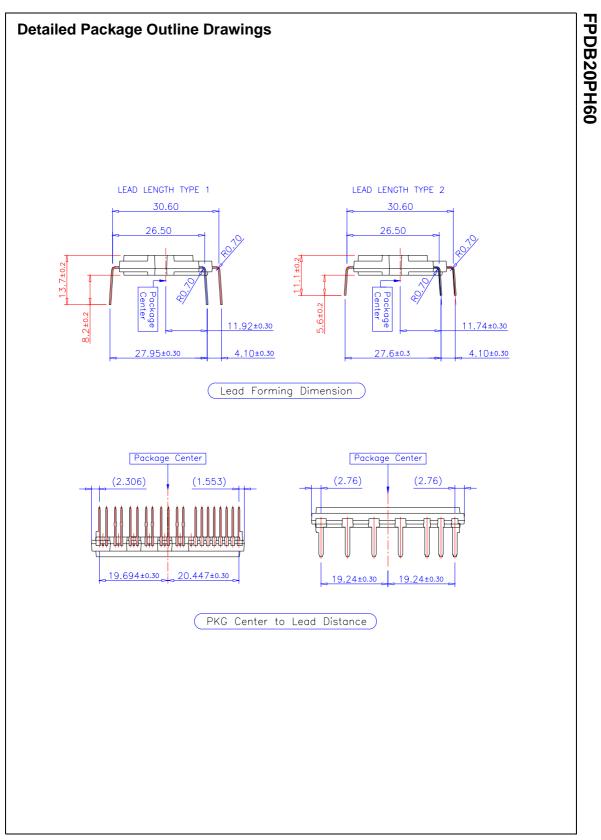


©2005 Fairchild Semiconductor Corporation

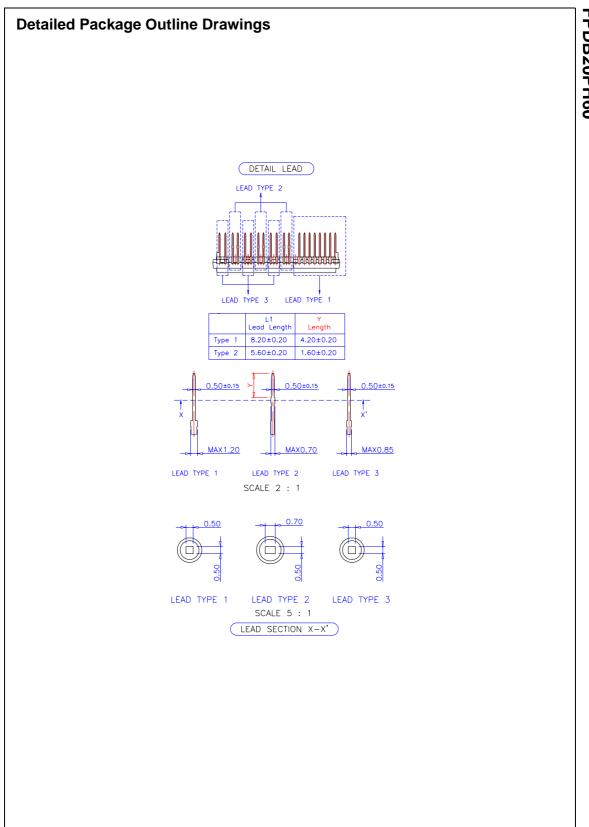


FPDB20PH60

©2005 Fairchild Semiconductor Corporation



©2005 Fairchild Semiconductor Corporation



FPDB20PH60

©2005 Fairchild Semiconductor Corporation

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST [®]	ISOPLANAR™	PowerSaver™	SuperSOT™-6
ActiveArray™	FASTr™	LittleFET™	PowerTrench [®]	SuperSOT™-8
Bottomless™	FPS™	MICROCOUPLER™	QFET [®]	SyncFET™
Build it Now™	FRFET™	MicroFET™	QS™	TCM™
CoolFET™	GlobalOptoisolator™	MicroPak™	QT Optoelectronics [™]	TinyLogic®
CROSSVOLT™	GTO™	MICROWIRE™	Quiet Series™	TINYOPTO™
DOME™	HiSeC™	MSX™	RapidConfigure™	TruTranslation™
EcoSPARK™	I ² C [™]	MSXPro™	RapidConnect™	UHC™
E ² CMOS [™]	i-Lo™	OCX™	µSerDes™	UltraFET [®]
EnSigna™	ImpliedDisconnect™	OCXPro™	ScalarPump™	UniFET™
FACT™	IntelliMAX™	OPTOLOGIC [®]	SILENT SWITCHER [®]	VCX™
FACT Quiet Serie	€S [™]	OPTOPLANAR™	SMART START™	Wire™
Aaroon the hear	d. Around the world.™	PACMAN™	SPM™	
The Power Fran		POP™	Stealth™	
Programmable A		Power247™	SuperFET™	
FIOGRAFIIITADIE P		PowerEdge™	SuperSOT™-3	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for ON Semiconductor manufacturer:

Other Similar products are found below :

1.5SMC82AT3G 74LCX574WM FST3126MX MC78L08ACP MMBTA42 FDD8424H_F085A NTZD3154NT1H KSA1015GRTA BAT42XV2 007851X 702607H MC33079DG MC34072DR2G MC34151P MC78L08ACDG 74VHC14MX 74VHC541MTCX FAN3111ESX FDMC86262P FDMD8530 FEBFL7733A_L53U021A FEBFOD8333 MM74HC138MX MMBZ5233B FOD3120SD FPAB30BH60B FQP2N80 1.5KE16AG MT9V115EBKSTCH-GEVB NB6L295MNGEVB NB7L1008MNGEVB NC7WZ126K8X NCL30000LED2GEVB NCN9252MUGEVB NCP1075PSRGEVB NCV4274CDT33RKG NCV887100D1R2G NDT2955 1N5339B NSIC2030JBT3G NV890231MWTXGEVB CAT4101AEVB KA7818ETU S3JB 2SC5569-TD-E FEBFL7734_L55L008A 1V5KE39CA FNB33060T AMIS30422DBGEVB AMIS3062XGEVK